

HCF65R360

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	650V N-Channel Super Junction Power MOSFET

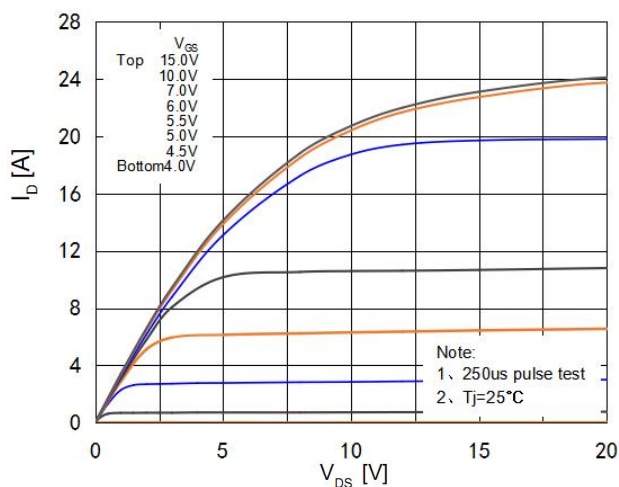
Electrical Characteristics(Tc=25°C unless otherwise noted)

Symbol	Parameter	Test Conditons	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-source Breakdown Voltage	V _{GS} =0V ,I _D =250μA	650	--	--	V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D =250μA (Referenced to 25°C)	--	0.68	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =650V,V _{GS} =0V	--	--	1	μA
		V _{DS} =520V,T _c =125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current,Forward	V _{GS} =+30V, V _{DS} =0V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current,Reverse	V _{GS} =-30V, V _{DS} =0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10 V, I _D =5.5A	--	300	360	mΩ
g _{FS}	Forward Transconductance	V _{DS} =20 V, I _D =5.5A (Note4)	--	6.9	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V,V _{GS} =0V, f=1.0MHz	--	830	--	pF
C _{oss}	Output Capacitance		--	970	--	pF
C _{rss}	Reverse Transfer Capacitance		--	18	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 325 V, I _D =11.0 A, R _G = 25 Ω (Note4,5)	--	12.7	--	ns
t _r	Turn-On Rise Time		--	33.6	--	ns
t _{d(off)}	Turn-Off Delay Time		--	61	--	ns
t _f	Turn-Off Fall Time		--	29.5	--	ns
Q _g	Total Gate Charge	V _{DS} = 520 V, I _D =11.0 A, V _{GS} = 10 V (Note4,5)	--	22.3	--	nC
Q _{gs}	Gate-Source Charge		--	5.7	--	nC
Q _{gd}	Gate-Drain Charge		--	10.2	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	11.0	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	44	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0V,I _S =11.0A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =11.0A, d I _F /dt=100A/μs (Note4)	--	357	--	ns
Q _{rr}	Reverse Recovery Charge		--	3.86	--	μC

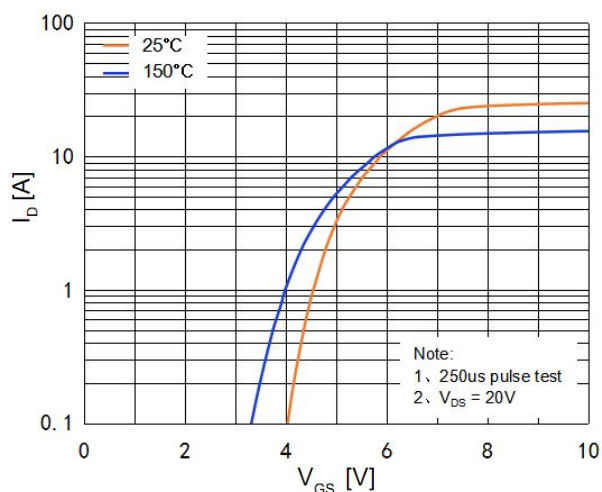
Notes:

- 1、Repetitive Rating:Pulse Width Limited by Maximum Junction Temperature.
- 2、 $L=14mH, I_{AS}=5.5A, V_{DD}=100V, R_G=25\Omega$, Starting $T_J=25^\circ C$.
- 3、 $I_{SD}\leq 11.0A, di/dt\leq 200A/\mu s, V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ C$.
- 4、Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- 5、Essentially Independent of Operating Temperature.

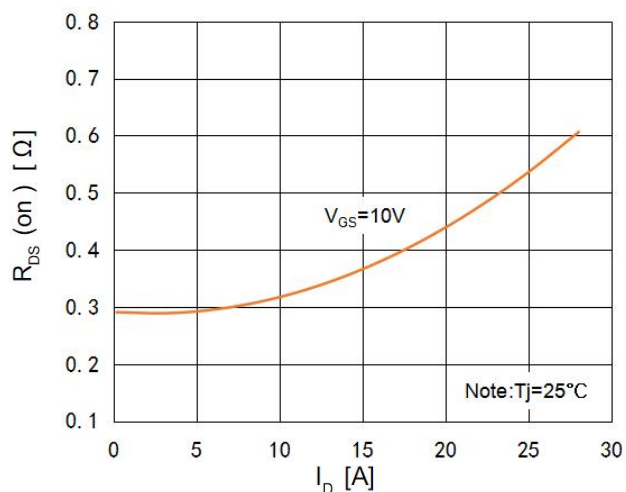
On-Regin Characteristics



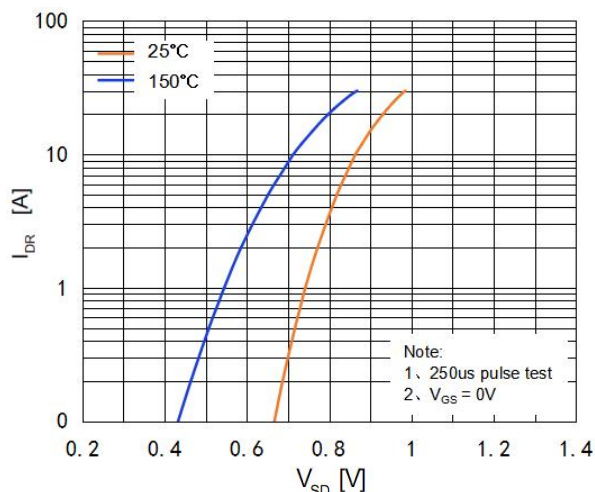
Transfer Characteristics



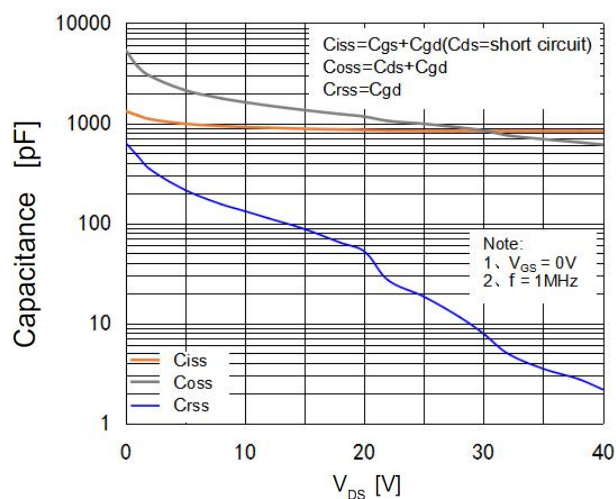
On-Resistance Variation vs. Drain Current and Gate Voltage



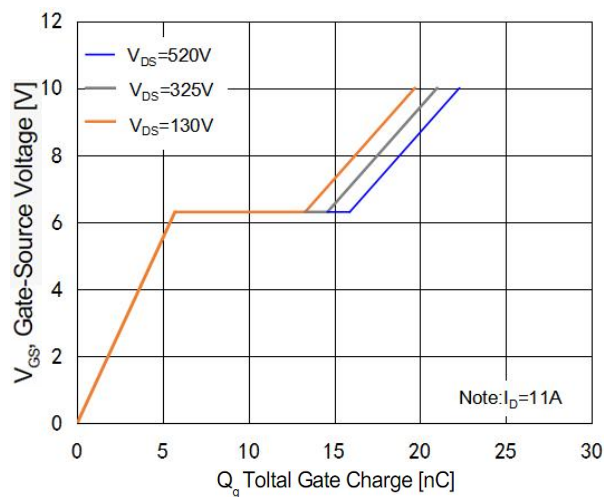
Body Diode Forward Voltage Variation vs. Source Current and Temperature



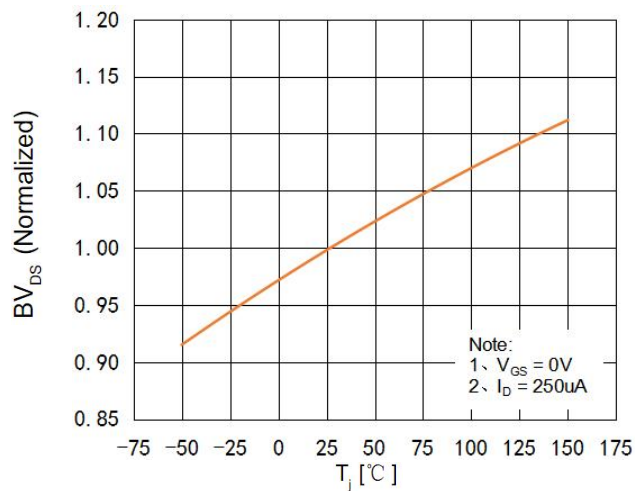
Capacitance Characteristics



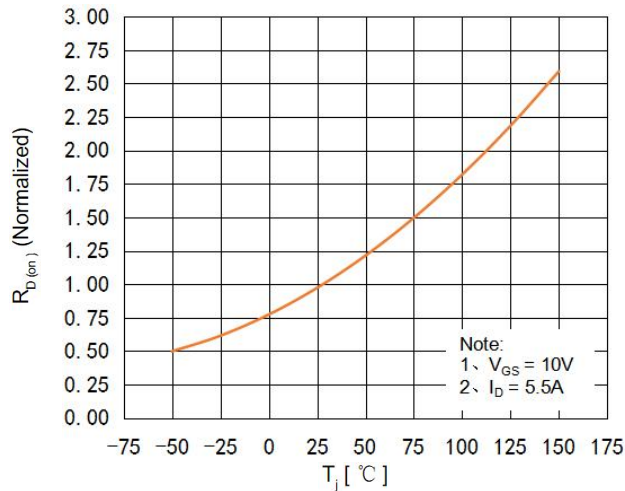
Gate Charge Characteristics



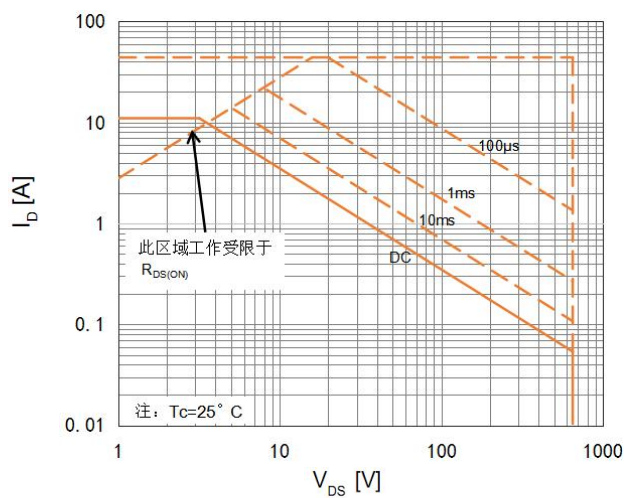
Breakdown Voltage Variation vs. Temperature



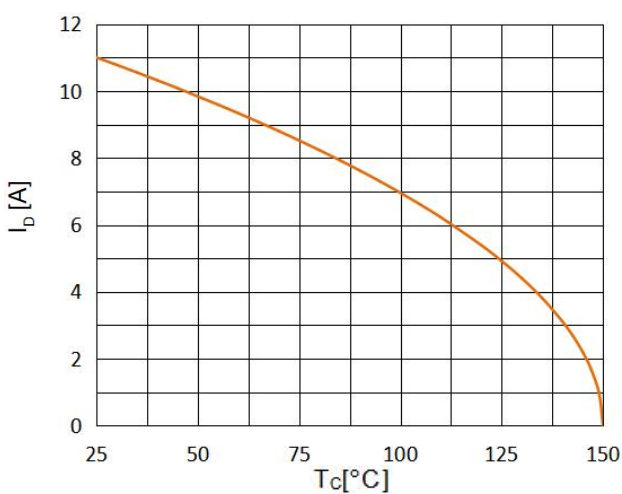
On-Resistance Variation vs. Temperature



Maximum Safe Operating Area



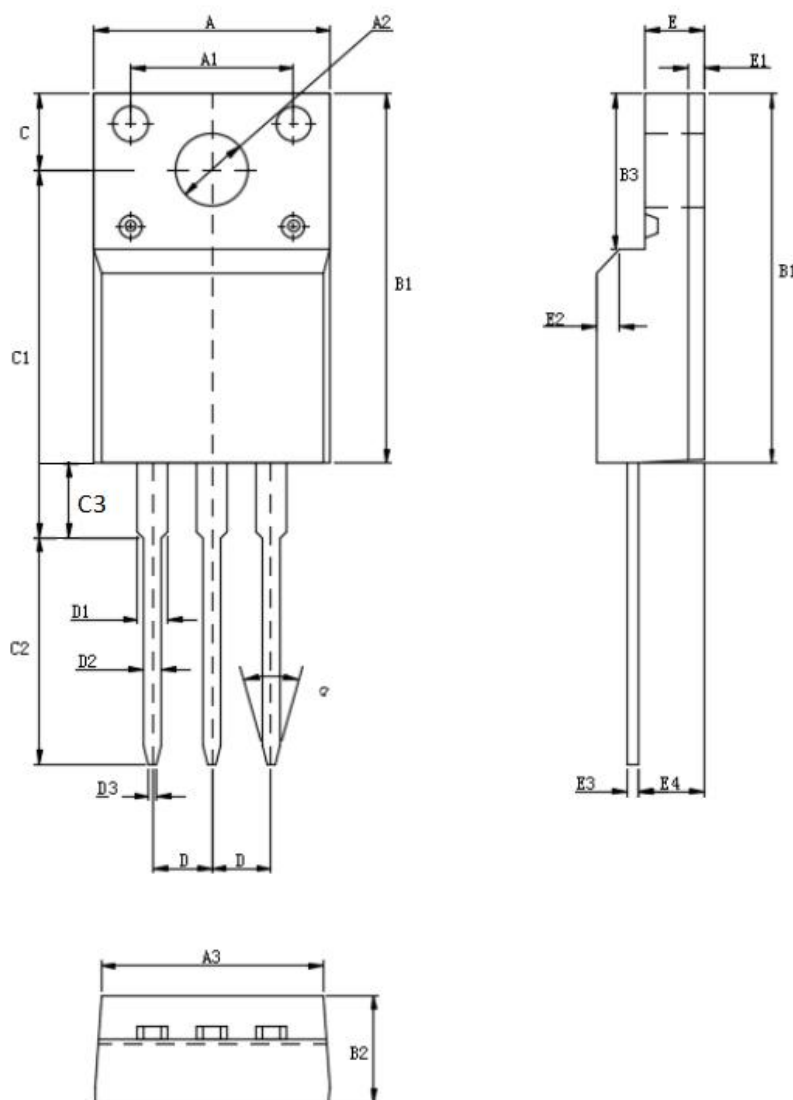
Maximum Drain Current Vs. Case Temperature



TO-220F Package Dimensions

UNIT: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	9.80		10.60	D		2.54	
A1		7.00		D1	1.15		1.47
A2	2.90		3.40	D2	0.60		0.90
A3	9.10		9.90	D3	0.20		0.50
B1	15.40		16.40	E	2.24		2.84
B2	4.35		4.95	E1		0.70	
B3	6.00		7.40	E2		1.0 × 45°	
C	3.00		3.70	E3	0.35		0.65
C1	15.00		17.00	E4	2.30		3.30
C2	8.80		10.80	α (度)		30°	
C3	2.60		3.60				



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注意事项：

- 1、在电路设计时请不要超过器件的最大额定值，否则会影响整机的可靠性。
- 2、MOSFET产品为静电敏感型器件，使用时应注意采取防静电保护措施，如佩戴防静电手环、设备接地等。
- 3、如需安装散热片，请注意控制扭力大小及散热片的平整度。
- 4、该规格书由华科公司制作，并可能不定期更改，恕不另行通知。
- 5、如有疑问，请及时联系我司销售代表。

版本履历表：

序号	版本号	修改时间	修改记录
1	V1.0	2022-12-20	首次发行